

LAYOUT & MATCHINGI. VARIATIONS & Effect. on MatchingA. Effect of lateral diffusion

$$L = L_{\text{drawn}} - DL$$

$$W = W_{\text{drawn}} - DW$$

- Choose  $L_{1\text{drawn}} = L_{2\text{drawn}}$

- Scale current using  $W_2/W_1$  ratio

$$\text{Choose } \frac{W_2}{W_1} = 10$$

$$\text{Want } I_{O2} = 10 I_{O1}$$

If you set  $W_{1\text{drawn}} = 1 \mu\text{m}$   
 $W_{2\text{drawn}} = 10 \mu\text{m}$ , then

$$\frac{I_{O2}}{I_{O1}} \sim \frac{W_{2\text{drawn}} - DW}{W_{1\text{drawn}} - DW}$$

$$= \frac{10 - DW}{1 - DW}$$

$$= \frac{10 - 0.1}{1 - 0.1} = 11 \quad (DW = 0.1 \mu\text{m})$$

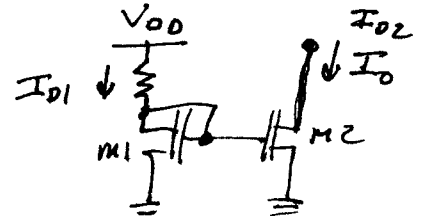
B. Threshold  $V_{TH}$  variations

$$V_{TH1} = V_{TH}$$

$$V_{TH2} = V_{TH} + \Delta V$$

$$\frac{I_{O2}}{I_{O1}} = \frac{(V_{GS} - V_{TH} - \Delta V)^2}{(V_{GS} - V_{TH})^2} \approx 1 - \frac{2\Delta V}{V_{GS} - V_{TH}} \quad \text{1st order } \Delta V$$

$\Rightarrow$  Want  $V_{GS} - V_{TH}$  large to minimize difference between  $I_{O2}$  &  $I_{O1}$



C.  $\mu_n C_{ox}$  ~~variations~~ variations

$$I_D = \frac{\mu_n C_{ox}}{2} \frac{W}{L} (V_{GS} - V_{TH})^2$$

$$\mu_{n2} C_{ox2} = \mu_{n1} C_{ox1} + \Delta$$

$$\frac{I_0}{I_{D1}} = 1 + \frac{\Delta}{\mu_{n1} C_{ox1}}$$

D.  $V_{DS}$  &  $\lambda$

$$I_D = \frac{\mu_n C_{ox}}{2} \frac{W}{L} (V_{GS} - V_{TH})^2 (1 + \lambda V_{DS})$$

$$\lambda = \lambda_c + \lambda_m$$

$\uparrow$  channel L modulation       $\uparrow$   $\mu_n$  modulation

Let  $V_{DS1} = 2V$ ,  $V_{DS2} = 4V$ ,  $\lambda_1 = 0.04$ ,  $\lambda_2 = 0.05$ .

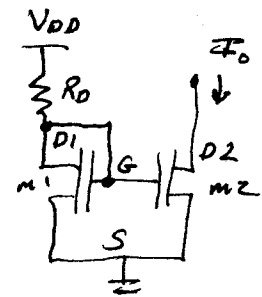
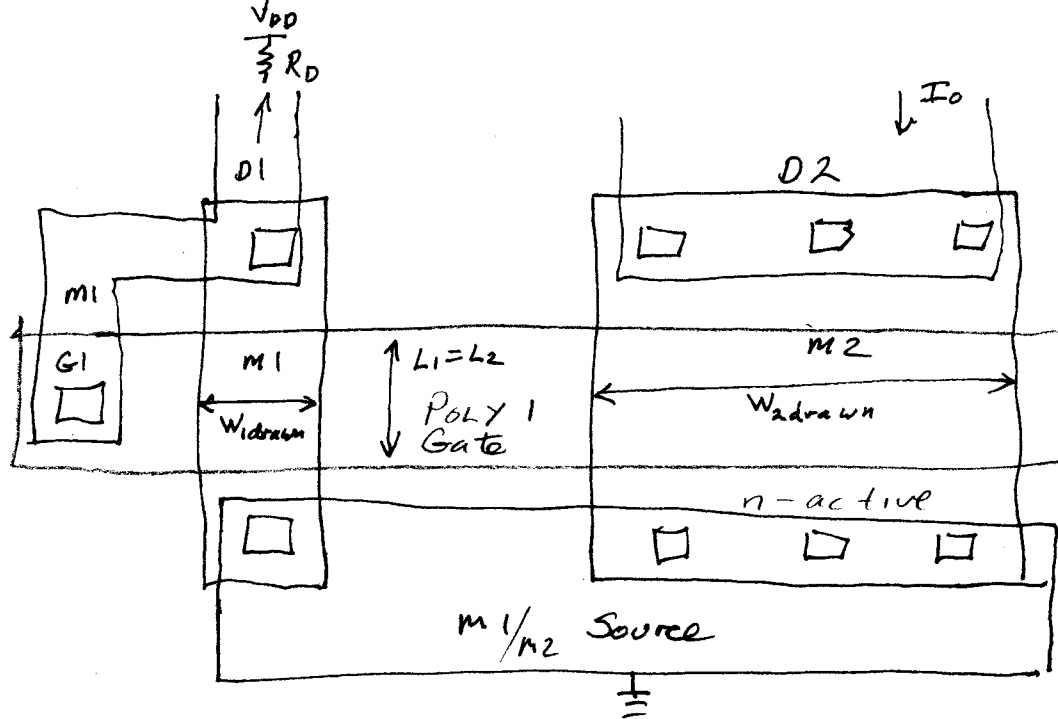
$$\begin{aligned} \frac{I_0}{I_{D1}} &= \frac{1 + \lambda_2 V_{DS2}}{1 + \lambda_1 V_{DS1}} = \frac{1 + (0.05) 4}{1 + (0.04) 2} \\ &= \frac{1.2}{1.08} = 1.11 \end{aligned}$$

- $\lambda$  is reduced for larger  $L$   
 $\lambda \downarrow$  as  $L \uparrow$ .
- Design for  $V_{DS1} \approx V_{DS2}$ .

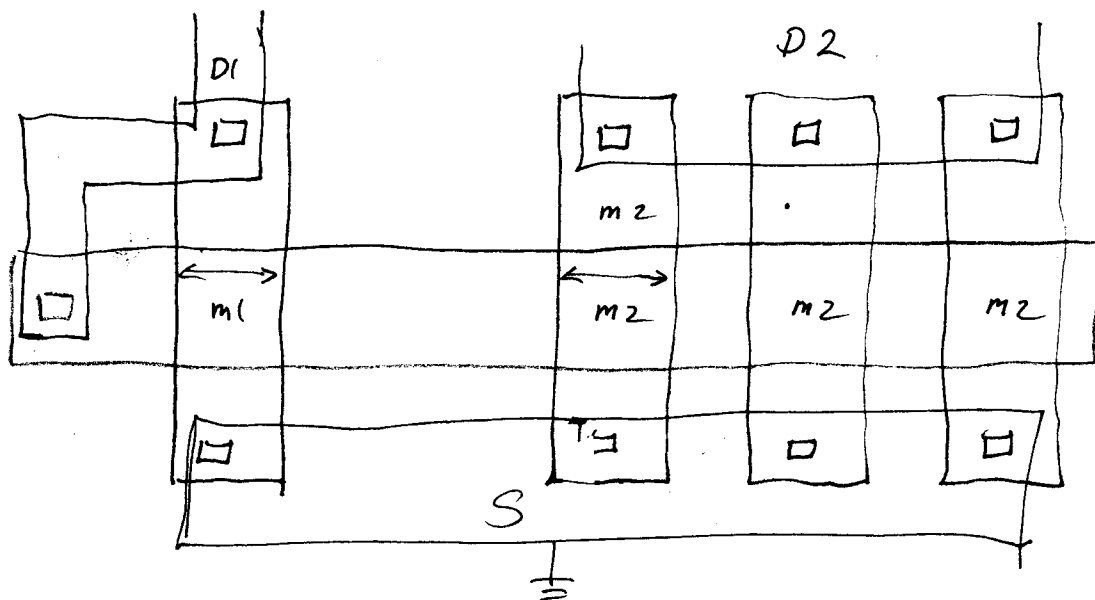
## II. LAYOUT SOLUTIONS (20.1.6) p 446

### A. LATERAL DIFFUSION

W 4



$$\frac{I_0}{I_{D1}} = \frac{W_{2drawn} - DW}{W_{1drawn} - DW} \neq \frac{W_{2drawn}}{W_{1drawn}}$$



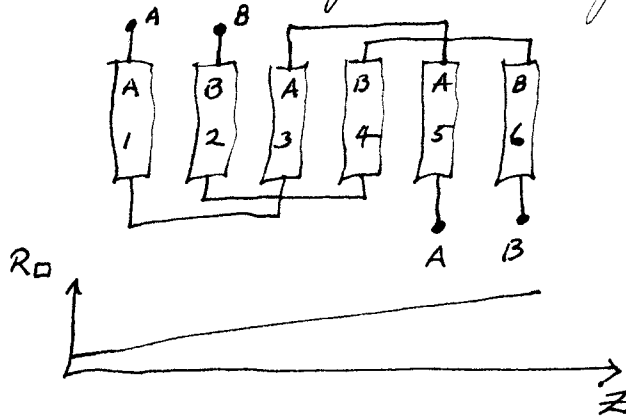
$$W_{1drawn} = W_{2drawn}$$

$$W_1 = W_{1drawn} - DW$$

$$W_2 = n(W_{1drawn} - DW)$$

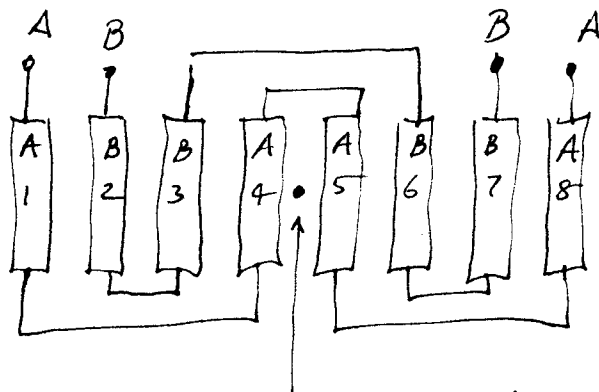
$$\frac{W_2}{W_1} = n$$

## REVIEW p. 138-9

A. Interdigitated Layout

$$R_A = 9$$

$$R_B = 12$$

B. Common Centroid

$$R_A = 18$$

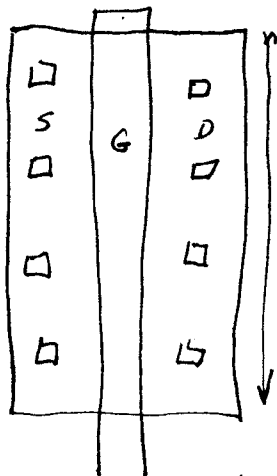
$$R_B = 18$$

Common center  
'Center of mass'

$$\frac{1}{A} \int_A d^2r \vec{F}$$

## B. General Matching & Layout.

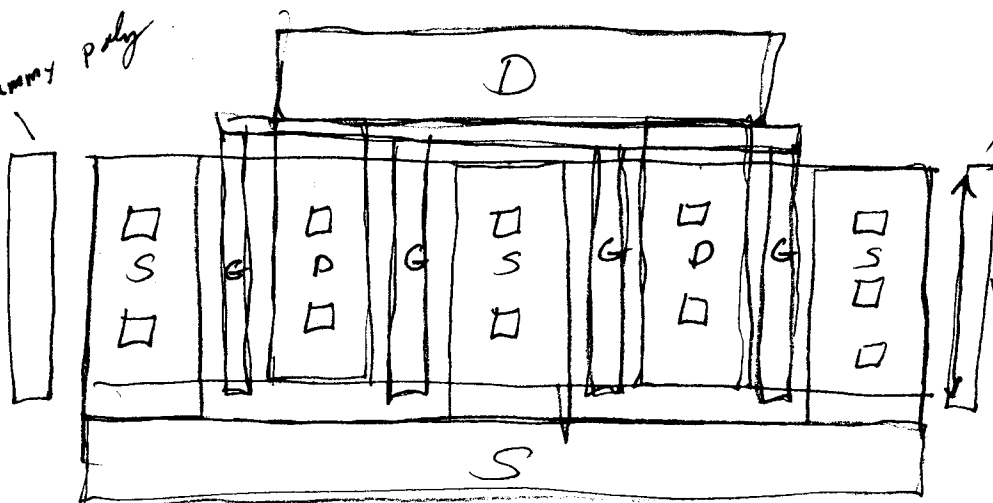
- Large W transistor layout



Large W

$$C_{sd} = C_{sd}' W$$

Dummy poly



Dummy poly  
(proximity effects)

$$W^* = W/4$$

$$C_{sp}^* = C_{sp}' \frac{3W}{4}$$

$$C_{db}^* = C_{db}' \frac{2W}{4}$$

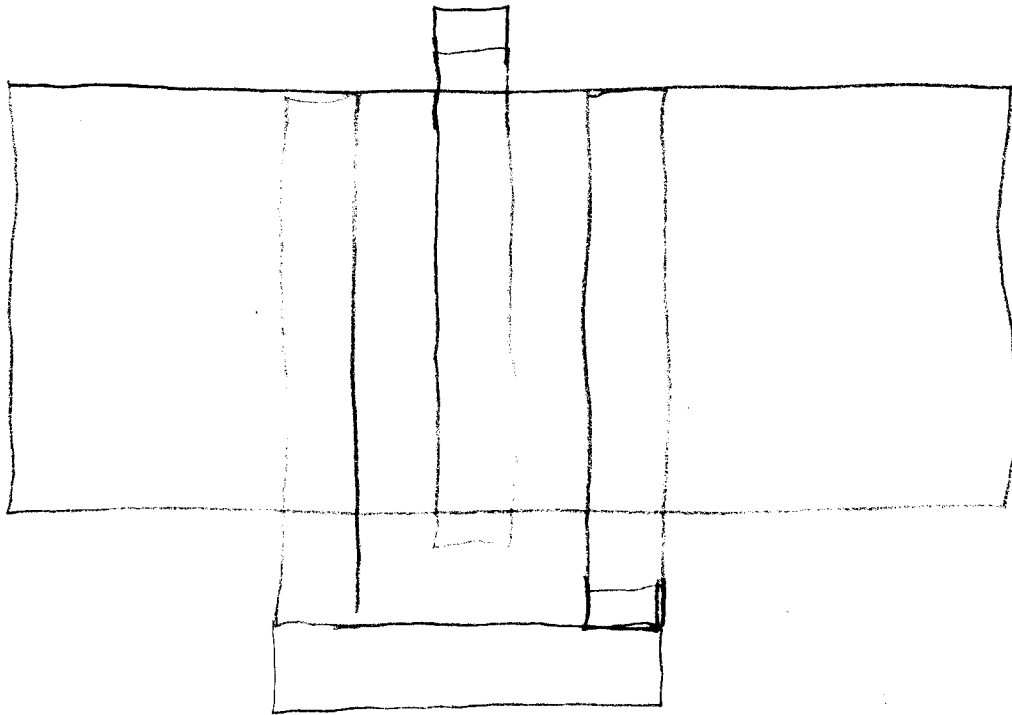
} Reduces parasitic  $C_{sb}$   
 $C_{db}$

Dummy Poly (Proximity Effect)

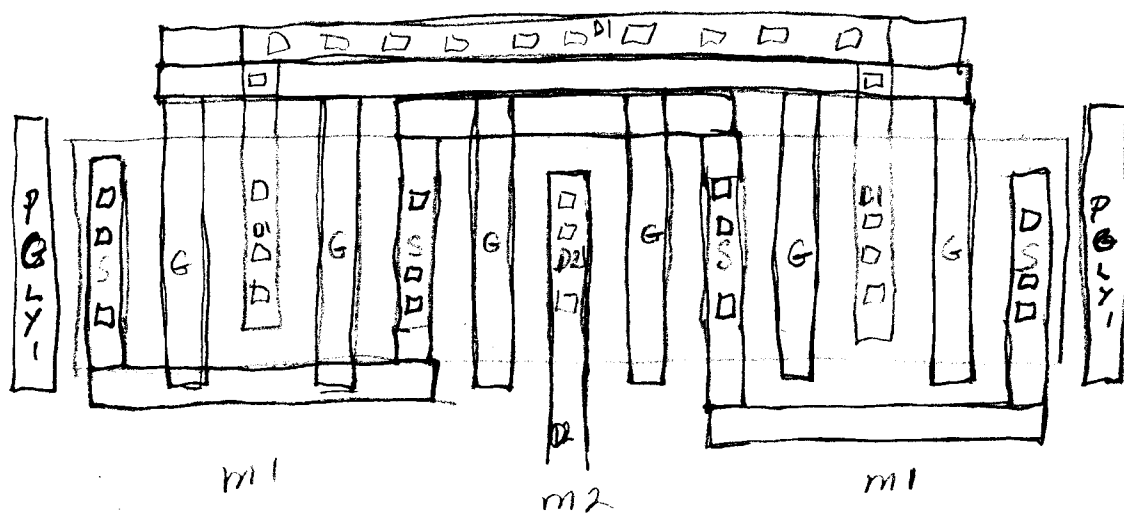
w/o dummy poly



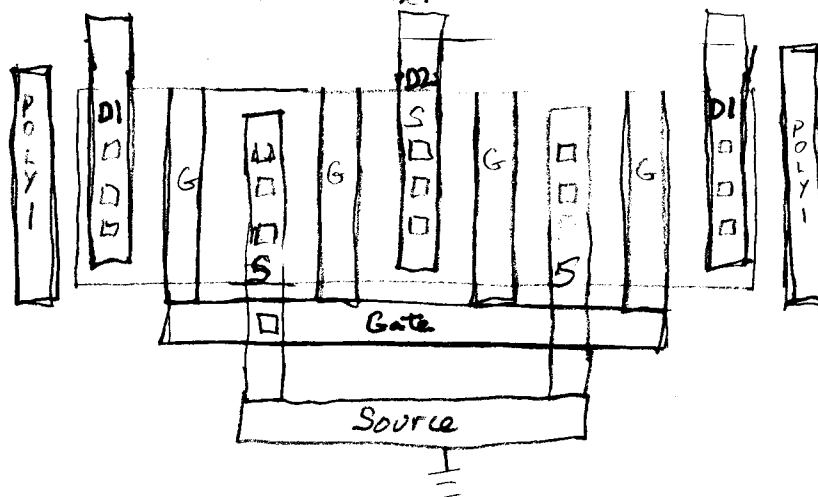
- matching
- transistors spatially close
- Same orientation
- Interdigitated FIG. 20.18 & 7.6
- Common Centroid (LAB THURS.)  
FIG. (7.7)
- Interdigitated layout



# Common Centroid



$$\frac{C_{ox}}{C_{ox1}} = C_{ox2}$$



dummy element  
for proximity  
effect